

| | L # | Hits | Search Text | DBs | Time Stamp |
|-----|-----|-------|---|---|---------------------|
| ✓ 1 | L1 | 118 | ("6589890") or ("5685941") or ("6077353") or ("6110836") or ("6346489") or ("6313042") or ("6372301") or ("6207558") or ("6368880") or ("6908865") or ("5504043") or ("5961793") or ("6426282") or ("6420260") or ("5242860") or ("5378660") or ("5360996") or ("5434044") or ("5521120") or ("5759360") or ("5972178") or ("5919342") or ("6071811") or ("5925225") or ("5943600") or ("6207027") or ("5882399") or ("6045666") or ("6059872") or ("6149777") or ("6899799") or ("5622608") or ("5766379") or ("5911113") or ("5959358") or ("6057237") or ("6037257") or ("6692617") or ("6605197") or ("6139699") or ("6387805") or ("6887353") or ("6057223") or ("6174811") or ("6232665") or ("6235163") or ("6328871") or ("6399479") or ("6398929") or ("6488823") or ("6200433") or ("6458251") or ("6350353") or ("6160315") or ("6436267") or ("6582569") or ("6566259") or ("6458255") or ("6368880") or ("6627050") or ("6790776") or ("6893541") or ("6793779") or ("6881673") or ("6919275")) .PN. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2005/09/02 13:12 |
| 2 | L2 | 1271 | (427/534, 536, 537) .CCLS. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2005/09/02 13:13 |
| 3 | L3 | 13367 | (438/710-733, 622, 637- 640, 653) .CCLS. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2005/09/02 13:25 |

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09/388, 989

2

| | L # | Hits | Search Text | DBs | Time Stamp |
|----|-----|--------|--|---|---------------------|
| 4 | L4 | 841 | (134/1.1,1.2).CCLS. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2005/09/02 13:25 |
| 5 | L5 | 677879 | plasma sputter\$5 (glow corona electric)adj discharg\$5 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2005/09/02 13:27 |
| 6 | L6 | 152616 | 5 same(clean\$5 preclean\$5 etch\$5) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2005/09/02 13:29 |
| 7 | L7 | 17922 | 6 same(Ar argon inert adj gas) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2005/09/02 13:33 |
| 8 | L8 | 16655 | 7 and (Ar argon) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2005/09/02 13:34 |
| 9 | L9 | 1732 | 6 same(He helium inert adj gas) same(H2 "H.sub.2" hydrogen) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2005/09/02 13:32 |
| 10 | L10 | 1394 | 6 same("He.m/c." helium inert adj gas) same(H2 "H.sub.2" hydrogen) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2005/09/02 13:34 |

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| | L # | Hits | Search Text | DBs | Time Stamp |
|----|-----|-------|--|---|---------------------|
| 11 | L11 | 893 | 10 and ("He.m/c." helium) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2005/09/02 13:35 |
| 12 | L12 | 680 | 8 and 11 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2005/09/02 13:33 |
| 13 | L13 | 45041 | 5 same(Ar argon inert adj gas)not 7 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2005/09/02 13:34 |
| 14 | L14 | 39140 | 13 and (Ar argon) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2005/09/02 13:34 |
| 15 | L15 | 5842 | 5 same("He.m/c." helium inert adj gas) same(H2 "H.sub.2" hydrogen) not10 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2005/09/02 13:35 |
| 16 | L16 | 3652 | 15 and ("He.m/c." helium) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2005/09/02 13:35 |
| 17 | L17 | 1951 | 14 and 16 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2005/09/02 13:36 |

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| | L # | Hits | Search Text | DBs | Time Stamp |
|----|----------------|----------------|---|---|---------------------|
| 18 | L18 | 62 | 2 and (12 or 17) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2005/09/02 13:36 |
| 19 | L19 | 61 | 2 and (12 or 17) not 1 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2005/09/02 13:36 |
| 20 | L20 | 221 | 3 and (12 or 17 or 18) not 1 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2005/09/02 13:37 |
| 21 | L21 | 221 | 3 and (12 or 17) not (1 or 18) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2005/09/02 13:38 |
| | L24 | 145 | 3 and 12 not (1 or 18) | | |
| 22 | L22 | 32 | 4 and (12 or 17) not (1 or 18 or 21) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2005/09/02 13:40 |
| 23 | L23 | 635 | 10 same 7 and ("He.m/c." helium)and (Ar argon) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2005/09/02 13:44 |
| 24 | L24 | 631 | 23 not 1 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2005/09/02 13:42 |

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| | L # | Hits | Search Text | DBs | Time Stamp |
|----|-----|------|---|---|---------------------|
| 25 | L25 | 471 | 23 not (1 or 18 Or 21 or 22) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2005/09/02 13:46 |
| 26 | L26 | 214 | 10 same 7 same (metal barrier Al aluminum Ti titanium) and("He.m/c." helium)and (Ar argon) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2005/09/02 13:46 |
| 27 | L27 | 160 | 26 not (1 or 18 or 21 or 22) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2005/09/02 13:46 |
| 28 | L28 | 311 | 25 not 27 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2005/09/02 13:47 |

PALM INTRANET

Day : Friday

Date: 9/2/2005

Time: 09:08:34

Inventor Name Search Result

Inventor Name
Search

Your Search was:

Last Name = COHEN

First Name = BARNEY

09/388,989

| Application# | Patent# | Status | Date Filed | Title | Inventor Name |
|---------------------|------------|----------------|------------|---|------------------|
| 08400329 | 5688358 | 150 | 03/08/1995 | R.F. PLASMA REACTOR WITH LARGER-THAN-WAFER PEDESTAL CONDUCTOR | COHEN, BARNEY |
| 08605507 | Not Issued | 161 | 02/26/1996 | METHODS FOR SUPPRESSING DETRIMENTAL EFFECTS OF CONDUCTIVE DEPOSITS ON INTERIOR SURFACES OF A PLASMA REACTOR | COHEN, BARNEY |
| 60085854 | Not Issued | 159 | 05/18/1998 | REDUCTION OF CUO IN A DUAL FREQUENCY ETCH CHAMBER | COHEN, BARNEY M |
| 09388989 | Not Issued | 135 | 09/02/1999 | SEQUENTIAL SPUTTER AND REACTIVE PRECLEANS OF VIAS AND CONTACTS | COHEN, BARNEY M. |
| 10075510 | 6589890 | 150 | 02/12/2002 | PRECLEANING PROCESS FOR METAL PLUG THAT MINIMIZES DAMAGE TO LOW-KAPPA DIELECTRIC | COHEN, BARNEY M. |
| 06534853 | Not Issued | 161 | 09/22/1983 | SEMICONDUCTOR DEVICES WITHOUT DIFFUSION PIPES | COHEN, BARNEY M. |
| 08252334 | Not Issued | 169 | 06/01/1994 | INDUCTIVELY COUPLED PLASMA REACTOR WITH TOP ELECTRODE FOR ENHANCING PLASMA IGNITION | COHEN, BARNEY M. |
| 08252963 | Not Issued | 166 | 06/02/1994 | INDUCTIVELY COUPLED PLASMA REACTOR WITH AN ELECTRODE FOR ENHANCING PLASMA IGNITION | COHEN, BARNEY M. |
| 08561144 | 5685941 | 150 | 11/21/1995 | INDUCTIVELY COUPLED PLASMA REACTOR WITH TOP ELECTRODE FOR ENHANCING PLASMA | COHEN, BARNEY M. |

| | | | | IGNITION | |
|-----------------|----------------|-----|------------|--|-----------------------------|
| <u>08646862</u> | <u>5763010</u> | 150 | 05/08/1996 | THERMAL POST-DEPOSITION TREATMENT OF HALOGEN-DOPED FILMS TO IMPROVE FILM STABILITY AND REDUCE HALOGEN MIGRATION TO INTERCONNECT LAYERS | COHEN, BARNEY M. |
| <u>09065758</u> | <u>6079354</u> | 150 | 04/24/1998 | THERMAL POST-DEPOSITION TREATMENT OF HALOGEN-DOPED FILMS TO IMPROVE FILM STABILITY AND REDUCE HALOGEN MIGRATION TO INTERCONNECT LAYERS | COHEN, BARNEY M. |
| <u>09082746</u> | <u>6547934</u> | 150 | 05/21/1998 | REDUCTION OF METAL OXIDE IN A DUAL FREQUENCY ETCH CHAMBER | COHEN, BARNEY M. |
| <u>09088759</u> | <u>6077353</u> | 150 | 06/02/1998 | PEDESTAL INSULATOR FOR A PRE-CLEAN CHAMBER | COHEN, BARNEY M. |
| <u>09206027</u> | Not Issued | 61 | 12/04/1998 | PLASMA PRECLEAN WITH ARGON, HELIUM, AND HYDROGEN GASES | COHEN, BARNEY M. |
| <u>09298065</u> | <u>6110836</u> | 150 | 04/22/1999 | REACTIVE PLASMA ETCH-CLEANING OF HIGH ASPECT RATIO OPENINGS | COHEN, BARNEY M. Au 1765 |
| <u>09309606</u> | Not Issued | 161 | 05/11/1999 | SEQUENTIAL SPUTTER AND REACTIVE PRECLEANS OF VIAS AND CONTACTS | COHEN, BARNEY M. |
| <u>09378364</u> | Not Issued | 161 | 08/20/1999 | SEQUENTIAL SPUTTER AND REACTIVE PRECLEANS OF VIAS AND CONTACTS | COHEN, BARNEY M. |
| <u>09388991</u> | <u>6346489</u> | 150 | 09/02/1999 | PRECLEANING PROCESS FOR METAL PLUG THAT MINIMIZES DAMAGE TO LOW-K DIELECTRIC | COHEN, BARNEY M. |
| <u>09390135</u> | <u>6313042</u> | 150 | 09/03/1999 | CLEANING CONTACT WITH SUCCESSIVE FLUORINE AND HYDROGEN PLASMAS | COHEN, BARNEY M. |

Inventor Search Completed: No Records to Display.

Search Another: Inventor

| | | |
|-----------|------------|--------|
| Last Name | First Name | |
| COHEN | BARNEY | Search |

PALM INTRANET

Day : Friday
 Date: 9/2/2005
 Time: 09:09:30

Inventor Name Search Result

Your Search was:

Last Name = LI

First Name = XIANGBING

| Application# | Patent# | Status | Date Filed | Title | Inventor Name |
|---------------------|------------|----------------|------------|--|---------------|
| 09206027 | Not Issued | 61 | 12/04/1998 | PLASMA PRECLEAN WITH ARGON, HELIUM, AND HYDROGEN GASES | LI, XIANGBING |
| 09218703 | 6372301 | 150 | 12/22/1998 | METHOD OF IMPROVING ADHESION OF DIFFUSION LAYERS ON FLUORINATED SILICON DIOXIDE | LI, XIANGBING |
| 09309606 | Not Issued | 161 | 05/11/1999 | SEQUENTIAL SPUTTER AND REACTIVE PRECLEANS OF VIAS AND CONTACTS | LI, XIANGBING |
| 09388989 | Not Issued | 135 | 09/02/1999 | SEQUENTIAL SPUTTER AND REACTIVE PRECLEANS OF VIAS AND CONTACTS | LI, XIANGBING |
| 09414651 | 6277253 | 150 | 10/06/1999 | EXTERNAL COATING OF TUNGSTEN OR TANTALUM OR OTHER REFRACTORY METAL ON IMP COILS | LI, XIANGBING |
| 09657792 | Not Issued | 161 | 09/08/2000 | Method of forming titanium nitride (TiN) films using metal-organic chemical vapor deposition (MOCVD) | LI, XIANGBING |
| 10097413 | Not Issued | 161 | 03/12/2002 | Adhesion of diffusion barrier and fluorinated silicon dioxide using hydrogen based preclean technology | LI, XIANGBING |

Inventor Search Completed: No Records to Display.

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PALM INTRANET

Day : Friday
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Inventor Name Search Result

Your Search was:

Last Name = RENGARAJAN

First Name = SURAJ

| Application# | Patent# | Status | Date Filed | Title | Inventor Name |
|---------------------|------------|----------------|------------|---|-------------------|
| 09309606 | Not Issued | 161 | 05/11/1999 | SEQUENTIAL SPUTTER AND REACTIVE PRECLEANS OF VIAS AND CONTACTS | RENGARAJAN, SURAJ |
| 09362923 | 6313033 | 150 | 07/27/1999 | IONIZED METAL PLASMA TA, TANX, W, AND WN X LINERS FOR GATE ELECTRODE APPLICATIONS | RENGARAJAN, SURAJ |
| 09388989 | Not Issued | 135 | 09/02/1999 | SEQUENTIAL SPUTTER AND REACTIVE PRECLEANS OF VIAS AND CONTACTS | RENGARAJAN, SURAJ |
| 09388991 | 6346489 | 150 | 09/02/1999 | PRECLEANING PROCESS FOR METAL PLUG THAT MINIMIZES DAMAGE TO LOW-K DIELECTRIC | RENGARAJAN, SURAJ |
| 09425082 | 6207558 | 150 | 10/21/1999 | BARRIER APPLICATIONS FOR ALUMINUM PLANARIZATION | RENGARAJAN, SURAJ |
| 09649507 | Not Issued | 161 | 08/28/2000 | METHOD AND APPARATUS FOR DEPOSITING A NITROGEN CONTAINING FILM FOR LOW-K APPLICATIONS | RENGARAJAN, SURAJ |
| 09775356 | Not Issued | 161 | 01/31/2001 | Method of obtaining low temperature alpha-Ta thin films using wafer bias | RENGARAJAN, SURAJ |
| 09784709 | 6368880 | 150 | 02/14/2001 | Barrier applications for aluminum planarization | RENGARAJAN, SURAJ |
| 09908829 | 6579730 | 150 | 07/18/2001 | MONITORING PROCESS FOR OXIDE REMOVAL | RENGARAJAN, SURAJ |
| 10015433 | 6908865 | 150 | 12/12/2001 | METHOD AND APPARATUS FOR CLEANING SUBSTRATES | RENGARAJAN, SURAJ |
| 10075510 | 6589890 | 150 | 02/12/2002 | PRECLEANING PROCESS FOR METAL PLUG THAT | RENGARAJAN, SURAJ |

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|-----------|---------------------|----------------|----------------|--|---|-------------------|
| | | | | MINIMIZES DAMAGE TO LOW-KAPPA DIELECTRIC | | |
| X | <u>10186270</u> | <u>6936842</u> | 150 | 06/26/2002 X | METHOD AND APPARATUS FOR PROCESS MONITORING | RENGARAJAN, SURAJ |
| | 10202778 | Not Issued | 161 | 07/25/2002 | Self-ionized and inductively-coupled plasma for sputtering and resputtering | RENGARAJAN, SURAJ |
| | <u>10246316</u> | <u>6911124</u> | 150 | 09/17/2002 7 | METHOD OF DEPOSITING A TAN SEED LAYER <i>TaN</i> | RENGARAJAN, SURAJ |
| | 10439021 | Not Issued | 161 | 05/14/2003 | Method and apparatus for sputter deposition | RENGARAJAN, SURAJ |
| X | <u>10495506</u> | Not Issued | 30 | 05/12/2004 X | Self-ionized and inductively-coupled plasma for sputtering and resputtering | RENGARAJAN, SURAJ |
| not clear | <u>10942358</u> | Not Issued | 30 | 09/16/2004 X | Compensation of spacing between magnetron and sputter target | RENGARAJAN, SURAJ |
| No | <u>11069348</u> | Not Issued | 30 | 02/28/2005 7 1 | Method of depositing a tantalum nitride / tantalum-diffusion barrier layer system | RENGARAJAN, SURAJ |
| No pre-de | <u>11184404</u> | Not Issued | 20 | 07/18/2005 ? | Method of depositing low resistivity barrier layers for copper interconnects | RENGARAJAN, SURAJ |
| No in 11 | <u>11184615</u> | Not Issued | 30 | 07/19/2005 | Self-ionized and inductively-coupled plasma for sputtering and resputtering | RENGARAJAN, SURAJ |
| | <u>60159986</u> | Not Issued | 159 | 10/18/1999 | PVD-IMP TUNGSTEN AND TUNGSTEN NITRIDE AS A LINER, BARRIER, AND/OR SEED LAYER FOR TUNGSTEN, ALUMINUM AND COPPER APPLICATIONS | RENGARAJAN, SURAJ |
| | <u>60301179</u> | Not Issued | 159 | 06/27/2001 | Method and apparatus for process monitoring | RENGARAJAN, SURAJ |
| | <u>60306698</u> | Not Issued | 159 | 07/20/2001 | Low resistivity tantalum nitride/tantalum bilayer stack | RENGARAJAN, SURAJ |
| | <u>60325712</u> | Not Issued | 159 | 09/28/2001 | Method and apparatus for plasma cleaning of copper | RENGARAJAN, SURAJ |
| | <u>60342608</u> | Not Issued | 159 | 12/21/2001 | Self-ionized and inductively-coupled plasma for sputtering and resputtering | RENGARAJAN, SURAJ |
| | <u>60380385</u> | Not Issued | 159 | 05/14/2002 | Method and apparatus for sputter deposition | RENGARAJAN, SURAJ |
| | <u>60529209</u> | Not Issued | 159 | 12/12/2003 | Compensation of spacing between magnetron and sputter target | RENGARAJAN, SURAJ |
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|----------|---------------|----|------------|---|----------------------|
| 60701316 | Not Issued | 20 | 07/21/2005 | Method and apparatus for in-situ substrate surface arc detection | RENGARAJAN, SURAJ |
|----------|---------------|----|------------|---|----------------------|

Inventor Search Completed: No Records to Display.

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|---------------------------------|------------------|-------------------|---------------------------------------|
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| | RENGARAJAN | SURAJ | |

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PALM INTRANET

Day : Friday
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 Time: 09:09:58

Inventor Name Search Result

Your Search was:

Last Name = NGAN

First Name = KENNY

| Application# | Patent# | Status | Date Filed | Title | Inventor Name |
|---------------------|------------|--------|------------|--|----------------------|
| 09593848 | Not Issued | 164 | 06/14/2000 | METHOD AND APPARATUS FOR BALANCING AN ELECTROSTATIC FORCE PRODUCED BY AN ELECTROSTATIC CHUCK | NGAN, KENNY K. |
| 10286688 | 6625003 | 150 | 11/01/2002 | METHOD AND APPARATUS FOR BALANCING AN ELECTROSTATIC FORCE PRODUCED BY AN ELECTROSTATIC CHUCK | NGAN, KENNY K. |
| 08312384 | 5504043 | 150 | 09/26/1994 | BARRIER LAYERS AND ALUMINUM CONTACTS | NGAN, KENNY K. |
| 08403085 | Not Issued | 166 | 03/13/1995 | TREATMENT OF A TITANIUM NITRIDE LAYER TO IMPROVE RESISTANCE TO ELEVATED TEMPERATURES | NGAN, KENNY K. |
| 08741708 | 5961793 | 150 | 10/31/1996 | METHOD OF REDUCING GENERATION OF PARTICULATE MATTER IN A SPUTTERING CHAMBER | NGAN, KENNY K. |
| 60139710 | Not Issued | 159 | 06/17/1999 | METHOD AND APPARATUS FOR BALANCING AN ELECTROSTATIC FORCE PRODUCED BY AN ELECTROSTATIC CHUCK | NGAN, KENNY K. |
| 08560083 | Not Issued | 164 | 11/17/1995 | METHOD FOR SPUTTER ETCHING SILICON WAFER WITH AN ELECTRICALLY CONDUCTING SURFACE AT A REDUCED PRESSURE | NGAN, KENNY K.T. |
| 08569760 | 5746460 | 150 | 12/08/1995 | END EFFECTOR FOR SEMICONDUCTOR WAFER TRANSFER DEVICE AND METHOD OF MOVING A WAFER WITH AN END | NGAN, KENNY KING TAI |

| | | | | EFFECTOR | |
|---------------------|------------|----------------|------------|--|----------------------|
| 08677588 | Not Issued | 161 | 07/09/1996 | METHOD FOR PROVIDING FULL-FACE HIGH DENSITY PLASMA DEPOSITION | NGAN, KENNY KING-TAI |
| 09388989 | Not Issued | 135 | 09/02/1999 | SEQUENTIAL SPUTTER AND REACTIVE PRECLEANS OF VIAS AND CONTACTS | NGAN, KENNY KING-TAI |
| 09565569 | 6426282 | 150 | 05/04/2000 | METHOD OF DEPOSITING LOW STRESS FILMS | NGAN, KENNY KING-TAI |
| 09578007 | 6267423 | 250 | 05/24/2000 | End effector for semiconductor wafer transfer device and method of moving a wafer with an end effector | NGAN, KENNY KING-TAI |
| 09597977 | Not Issued | 161 | 06/20/2000 | Method of producing smooth titanium nitride films having low resistivity | NGAN, KENNY KING-TAI |
| 09695941 | 6420260 | 150 | 10/24/2000 | TI/TINX UNDERLAYER WHICH ENABLES A HIGHLY <111> ORIENTED ALUMINUM INTERCONNECT | NGAN, KENNY KING-TAI |
| 10046954 | Not Issued | 41 | 01/14/2002 | Semiconductor wafer preheating | NGAN, KENNY KING-TAI |
| 10075510 | 6589890 | 150 | 02/12/2002 | PRECLEANING PROCESS FOR METAL PLUG THAT MINIMIZES DAMAGE TO LOW-KAPPA DIELECTRIC | NGAN, KENNY KING-TAI |
| 10097413 | Not Issued | 161 | 03/12/2002 | Adhesion of diffusion barrier and fluorinated silicon dioxide using hydrogen based preclean technology | NGAN, KENNY KING-TAI |
| 10126333 | Not Issued | 61 | 04/19/2002 | Reducing particle generation during sputter deposition | NGAN, KENNY KING-TAI |
| 10140732 | Not Issued | 161 | 05/07/2002 | Method of producing smooth titanium nitride films having low resistivity | NGAN, KENNY KING-TAI |
| 10229879 | 6672864 | 150 | 08/27/2002 | METHOD AND APPARATUS FOR PROCESSING SUBSTRATES IN A SYSTEM HAVING HIGH AND LOW PRESSURE AREAS | NGAN, KENNY KING-TAI |
| 10256660 | Not Issued | 161 | 09/27/2002 | Method for modulating stress in films deposited using a physical vapor deposition (PVD) process | NGAN, KENNY KING-TAI |
| 10748931 | Not Issued | 168 | 12/24/2003 | Method and apparatus for processing substrates in a system | NGAN, KENNY KING-TAI |

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|-----------------|----------------|-----|------------|--|----------------------|
| | | | | having high and low pressure areas | |
| <u>10799361</u> | Not Issued | 30 | 03/12/2004 | Refurbishment of sputtering targets | NGAN, KENNY KING-TAI |
| <u>10888941</u> | 6945857 | 150 | 07/08/2004 | POLISHING PAD CONDITIONER AND METHODS OF MANUFACTURE AND RECYCLING | NGAN, KENNY KING-TAI |
| <u>10901319</u> | Not Issued | 30 | 07/27/2004 | Reduced oxygen arc spray | NGAN, KENNY KING-TAI |
| <u>10910096</u> | Not Issued | 30 | 08/02/2004 | Coating for aluminum component | NGAN, KENNY KING-TAI |
| <u>10962890</u> | Not Issued | 41 | 10/12/2004 | Polishing pad conditioner with shaped abrasive patterns and channels | NGAN, KENNY KING-TAI |
| <u>10968367</u> | Not Issued | 30 | 10/18/2004 | In-situ monitoring of target erosion | NGAN, KENNY KING-TAI |
| <u>11130493</u> | Not Issued | 30 | 05/16/2005 | Method and apparatus for improving sidewall coverage during sputtering in a chamber having an inductively coupled plasma | NGAN, KENNY KING-TAI |
| <u>60316632</u> | Not Issued | 159 | 08/31/2001 | Method and apparatus for processing substrates in a system having high and low pressure areas | NGAN, KENNY KING-TAI |
| <u>07735397</u> | <u>5242860</u> | 150 | 07/24/1991 | METHOD FOR THE FORMATION OF TIN BARRIER LAYER WITH PREFERENTIAL (111) CRYSTALLOGRAPHIC ORIENTATION | NGAN, KENNY KING-TAI |
| <u>08017081</u> | <u>5378660</u> | 150 | 02/12/1993 | BARRIER LAYERS AND ALUMINUM CONTACTS | NGAN, KENNY KING-TAI |
| <u>08065309</u> | <u>5360996</u> | 150 | 05/21/1993 | TITANIUM NITRIDE/TITANIUM SILICIDE MULTIPLE LAYER BARRIER WITH PREFERENTIAL (111) CRYSTALLOGRAPHIC ORIENTATION ON TITANIUM NITRIDE SURFACE | NGAN, KENNY KING-TAI |
| <u>08253515</u> | <u>5434044</u> | 250 | 06/03/1994 | METHOD FOR THE FORMATION OF TIN BARRIER LAYER WITH PREFERENTIAL (111) CRYSTALLOGRAPHIC ORIENTATION | NGAN, KENNY KING-TAI |
| <u>08310180</u> | Not Issued | 166 | 09/21/1994 | BARRIER LAYERS AND ALUMINUM CONTACTS | NGAN, KENNY KING-TAI |
| <u>08377566</u> | <u>5521120</u> | 150 | 01/24/1995 | METHOD FOR THE | NGAN, KENNY |

| | | | | | |
|---------------------|-----------------------|----------------|------------|--|----------------------|
| | | | | FORMATION OF TIN BARRIER LAYER WITH PREFERENTIAL (111) CRYSTALLOGRAPHIC ORIENTATION | KING-TAI |
| 08402676 | 5759360 | 150 | 03/13/1995 | WAFAER <u>CLEAN SPUTTERING</u> PROCESS | NGAN, KENNY KING-TAI |
| 08481550 | 5972178 | 250 | 06/07/1995 | CONTINUOUS PROCESS FOR FORMING <u>IMPROVED</u> TITANIUM NITRIDE BARRIER LAYERS | NGAN, KENNY KING-TAI |
| 08542573 | Not Issued | 166 | 10/13/1995 | METHOD FOR GENERATING AN EUTECTIC REACTION WITHIN A PHYSICAL VAPOR DEPOSITION SYSTEM | NGAN, KENNY KING-TAI |
| 08551688 | Not Issued | 166 | 11/01/1995 | BARRIER LAYERS AND ALUMINUM CONTACTS | NGAN, KENNY KING-TAI |
| 08576953 | 5697427 | 150 | 12/22/1995 | APPARATUS AND METHOD FOR COOLING A SUBSTRATE | NGAN, KENNY KING-TAI |
| 08682845 | 5707498 | 150 | 07/12/1996 | AVOIDING CONTAMINATION FROM INDUCTION COIL IN IONIZED SPUTTERING | NGAN, KENNY KING-TAI |
| 08805181 | 5919342 | 250 | 02/26/1997 | METHOD FOR DEPOSITING GOLDEN TITANIUM NITRIDE | NGAN, KENNY KING-TAI |
| 08806966 | 6071811 | 150 | 02/26/1997 | DEPOSITION OF TITANIUM NITRIDE FILMS HAVING IMPROVED UNIFORMITY | NGAN, KENNY KING-TAI |
| 08824465 | Not Issued | 161 | 03/26/1997 | BARRIER LAYERS AND ALUMINUM CONTACTS | NGAN, KENNY KING-TAI |
| 08824911 | Not Issued | 161 | 03/27/1997 | TI/TIN/TINX UNDERLAYER WHICH ENABLES A HIGHLY (111) ORIENTED ALUMINUM INTERCONNECT | NGAN, KENNY KING-TAI |
| 08825216 | 5925225 | 150 | 03/27/1997 | SMOOTH TITANIUM NITRIDE FILMS HAVING LOW RESISTIVITY | NGAN, KENNY KING-TAI |
| 08833404 | Not Issued | 161 | 04/04/1997 | MEHTOD AND APPARATUS FOR REDUCING THE FIRST WAFER EFFECT | NGAN, KENNY KING-TAI |
| 08840439 | 5943600 | 150 | 03/31/1997 | TREATMENT OF A TITANIUM NITRIDE LAYER TO IMPROVE RESISTANCE TO ELEVATED TEMPERATURES | NGAN, KENNY KING-TAI |
| 08847233 | 6207027 | 150 | 05/07/1997 | METHOD TO REDUCE OVERHEAD TIME IN AN ION METAL PLASMA PROCESS | NGAN, KENNY KING-TAI |

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First Name = KENNY

| Application# | Patent# | Status | Date Filed | Title | Inventor Name |
|---------------------|-----------------------|----------------|-----------------------|--|---------------------------------|
| 08864790 | Not Issued | 161 | 05/29/1997 | METHOD FOR GENERATING AN EUTECTIC REACTION WITHIN A PHYSICAL VAPOR DEPOSITION SYSTEMS | NGAN, KENNY KING-TAI |
| 08897750 | Not Issued | 161 | 07/21/1997 | END EFFECTOR FOR SEMICONDUCTOR WAFER TRANSFER DEVICE AND METHOD OF MOVING A WAFER WITH AN END EFFECTOR | NGAN, KENNY KING-TAI |
| 08914580 | 6176978 | 150 | 08/18/1997 | PASTING METHOD | NGAN, KENNY KING-TAI |
| 08924487 | 5882399 | 150 | 08/23/1997 | METHOD OF FORMING A BARRIER LAYER WHICH ENABLES A CONSISTENTLY HIGHLY ORIENTED CRYSTALLINE STRUCTURE IN A METALLIC INTERCONNECT | NGAN, KENNY KING-TAI |
| 08977007 | 6045666 | 150 | 11/24/1997 | ALUMINUM HOLE FILLING METHOD USING IONIZED METAL ADHESION LAYER | NGAN, KENNY KING-TAI |
| 09003014 | Not Issued | 163 | 01/05/1998 | METHOD OF DEPOSITING A TITANIUM NITRIDE FILM HAVING LOW STRESS AND PROVIDING HIGH BOTTOM COVERAGE IN HIGH ASPECT RATIO FEATURES | NGAN, KENNY KING-TAI |
| 09010359 | 6059872 | 150 | 01/21/1998 | SMOOTH TITANIUM NITRIDE FILMS HAVING LOW RESISTIVITY | NGAN, KENNY KING-TAI |
| 09206027 | Not Issued | 61 | 12/04/1998 | PLASMA PRECLEAN WITH ARGON, HELIUM, AND HYDROGEN GASES | NGAN, KENNY KING-TAI |
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|---------------------|------------|-----|------------|--|----------------------|
| 09218703 | 6372301 | 150 | 12/22/1998 | METHOD OF IMPROVING ADHESION OF DIFFUSION LAYERS ON FLUORINATED SILICON DIOXIDE | NGAN, KENNY KING-TAI |
| 09294441 | 6149777 | 150 | 01/25/1999 | METHOD OF PRODUCING SMOOTH TITANIUM NITRIDE FILMS HAVING LOW RESISTIVITY | NGAN, KENNY KING-TAI |
| 09298065 | 6110836 | 150 | 04/22/1999 | REACTIVE PLASMA ETCH CLEANING OF HIGH ASPECT RATIO OPENINGS | NGAN, KENNY KING-TAI |
| 09309606 | Not Issued | 161 | 05/11/1999 | SEQUENTIAL SPUTTER AND REACTIVE PRECLEANS OF VIAS AND CONTACTS | NGAN, KENNY KING-TAI |
| 09388991 | 6346489 | 150 | 09/02/1999 | PRECLEANING PROCESS FOR METAL PLUG THAT MINIMIZES DAMAGE TO LOW-K DIELECTRIC | NGAN, KENNY KING-TAI |
| 09390135 | 6313042 | 150 | 09/03/1999 | CLEANING CONTACT WITH SUCCESSIVE FLUORINE AND HYDROGEN PLASMAS | NGAN, KENNY KING-TAI |
| 09425583 | 6149784 | 150 | 10/22/1999 | SPUTTERING CHAMBER SHIELD PROMOTING RELIABLE PLASMA IGNITION | NGAN, KENNY KING-TAI |
| 10263167 | 6899799 | 150 | 10/02/2002 | METHOD AND APPARATUS FOR IMPROVING SIDEWALL COVERAGE DURING SPUTTERING IN A CHAMBER HAVING AN INDUCTIVELY COUPLED PLASMA | NGAN, KENNY KING-TAI |
| 10900532 | Not Issued | 20 | 07/27/2004 | Profile detection and refurbishment of deposition targets | NGAN, KENNY KING-TAI |

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|---------------------|---------------------------|----------------|-----------------------|--|-------------------------|
| 08219131 | 5622608 | 150 | 05/05/1994 7 | PROCESS OF MAKING OXIDATION RESISTANT HIGH CONDUCTIVITY COPPER LAYERS | DING, PEIJUN |
| 08478491 | 5766379 | 150 | 06/07/1995 7 | PASSIVATED COPPER CONDUCTIVE LAYERS FOR MICROELECTRONIC APPLICATIONS AND METHODS OF MANUFACTURING SAME | DING, PEIJUN |
| 08677760 | 5736021 | 150 | 07/10/1996 X | ELECTRICALLY FLOATING SHIELD IN A PLASMA REACTOR | DING, PEIJUN |
| 08756468 | Not Issued | 168 | 11/26/1996 | COATED DEPOSITION CHAMBER EQUIPMENT | DING, PEIJUN |
| 08761584 | Not Issued | 161 | 12/06/1996 | MODIFIED PHYSICAL VAPOR DEPOSITION CHAMBER AND METHOD OF DEPOSITING MATERIALS AT LOW PRESSURE | DING, PEIJUN |
| 08820512 | 5911113 | 150 | 03/18/1997 7 | SILICON-DOPED TITANIUM WETTING LAYER FOR ALUMINUM PLUG | DING, PEIJUN |
| 08837770 | 5959358 | 150 | 04/22/1997 7 | OXIDATION RESISTANT HIGH CONDUCTIVITY COPPER LAYERS FOR MICROELECTRONIC APPLICATIONS AND PROCESS OF MAKING SAME | DING, PEIJUN |
| 08841058 | 6057237 | 150 | 04/29/1997 7 | TANTALUM-CONTAINING BARRIER LAYERS FOR COPPER | DING, PEIJUN |
| 08853191 | 6037257 | 150 | 05/08/1997 7 | SPUTTER DEPOSITION AND ANNEALING OF COPPER | DING, PEIJUN |

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|----------|------------|-----|------------|--|--------------|
| | | | | ALLOY METALLIZATION | |
| 08854008 | 6692617 | 150 | 05/08/1997 | SUSTAINED SELF-SPUTTERING REACTOR HAVING AN INCREASED DENSITY PLASMA | DING, PEIJUN |
| 08855059 | 6605197 | 150 | 05/13/1997 | METHOD OF SPUTTERING COPPER TO FILL TRENCHES AND VIAS | DING, PEIJUN |
| 08863451 | 6139699 | 150 | 05/27/1997 | SPUTTERING METHODS FOR DEPOSITING STRESS TUNABLE TANTALUM AND TANTALUM NITRIDE FILMS | DING, PEIJUN |
| 08878143 | 6387805 | 150 | 06/18/1997 | COPPER-ALLOY SEED LAYER FOR COPPER METALLIZATION | DING, PEIJUN |
| 08939396 | 5879523 | 150 | 09/29/1997 | CERAMIC COATED METALLIC INSULATOR PARTICULARLY USEFUL IN A PLASMA SPUTTER REACTOR | DING, PEIJUN |
| 08978792 | Not Issued | 161 | 11/26/1997 | DAMAGE-FREE SCULPTURED COATING DEPOSITION | DING, PEIJUN |
| 08995108 | 6887353 | 150 | 12/19/1997 | TAILORED BARRIER LAYER WHICH PROVIDES IMPROVED COPPER INTERCONNECT ELECTROMIGRATION RESISTANCE | DING, PEIJUN |
| 09013823 | 6110821 | 150 | 01/27/1998 | METHOD FOR FORMING TITANIUM SILICIDE IN SITU | DING, PEIJUN |
| 09021666 | 6057223 | 150 | 02/10/1998 | PASSIVATED COPPER CONDUCTIVE LAYERS FOR MICROELECTRONIC APPLICATIONS | DING, PEIJUN |
| 09024530 | 6077404 | 150 | 02/17/1998 | REFLOW CHAMBER AND PROCESS | DING, PEIJUN |
| 09039695 | 6506287 | 150 | 03/16/1998 | OVERLAP DESIGN OF ONE-TURN COIL | DING, PEIJUN |
| 09047107 | Not Issued | 163 | 03/24/1998 | TANTALUM-CONTAINING BARRIER LAYERS FOR COPPER | DING, PEIJUN |
| 09058432 | Not Issued | 161 | 04/10/1998 | BARRIER LAYERS FOR COPPER | DING, PEIJUN |
| 09123010 | Not Issued | 161 | 07/27/1998 | SPUTTERING TARGET ASSEMBLY | DING, PEIJUN |
| 09160638 | Not Issued | 161 | 09/24/1998 | ULTRA-LOW RESISTIVITY TANTALUM FILMS AND | DING, PEIJUN |

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|---------------------|------------|----------------|-----------------|---|--------------|
| | | | | METHODS FOR THEIR DEPOSITION | |
| 09191078 | Not Issued | 161 | 11/12/1998 | TANTALUM-CONTAINING BARRIER LAYERS FOR COPPER USING HIGH PURITY TANTALUM TARGETS FOR SPUTTERING | DING, PEIJUN |
| 09191253 | 6149776 | 150 | 11/12/1998 N | COPPER SPUTTERING TARGET | DING, PEIJUN |
| 09199965 | 6184137 | 250 | 11/25/1998 N | STRUCTURE AND METHOD FOR IMPROVING LOW TEMPERATURE COPPER REFLOW IN SEMICONDUCTOR FEATURES | DING, PEIJUN |
| 09204323 | 6174811 | 250 | 12/02/1998 7 | INTEGRATED DEPOSITION PROCESS FOR COPPER METALLIZATION | DING, PEIJUN |
| 09208663 | Not Issued | 161 | 12/10/1998 | HIGH-DENSITY METAL SPUTTERING AT LOW PRESSURE | DING, PEIJUN |
| 09253585 | Not Issued | 161 | 02/19/1999 | USING ELECTROPLATED CU AS COLD LAYER FOR COLD/HOT DEPOSITION | DING, PEIJUN |
| 09261700 | 6193811 | 150 | 03/03/1999 N | METHOD FOR IMPROVED CHAMBER BAKE-OUT AND COOL-DOWN | DING, PEIJUN |
| 09309606 | Not Issued | 161 | 05/11/1999 | SEQUENTIAL SPUTTER AND REACTIVE PRECLEANS OF VIAS AND CONTACTS | DING, PEIJUN |
| 09326395 | 6277198 | 150 | 06/04/1999 X | USE OF TAPERED SHADOW CLAMP RING TO PROVIDE IMPROVED PHYSICAL VAPOR DEPOSITION SYSTEM | DING, PEIJUN |
| 09328117 | 6232665 | 250 | 06/08/1999 ? | SILICON-DOPED TITANIUM WETTING LAYER FOR ALUMINUM PLUG | DING, PEIJUN |
| 09350556 | 6235163 | 250 | 07/09/1999 ? | METHODS AND APPARATUS FOR IONIZED METAL PLASMA COPPER DEPOSITION WITH ENHANCED IN-FILM PARTICLE PERFORMANCE | DING, PEIJUN |
| 09350619 | 6376807 | 150 | 07/09/1999 X | ENHANCED COOLING IMP COIL SUPPORT | DING, PEIJUN |
| 09362923 | 6313033 | 150 | 07/27/1999 X | IONIZED METAL PLASMA TA, TANX, W, AND WN X LINERS FOR GATE | DING, PEIJUN |

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|---------------------|------------|-----|------------------|--|--------------|
| | | | | ELECTRODE APPLICATIONS | |
| 09373103 | Not Issued | 161 | 08/12/1999 | METHOD AND APPARATUS FOR CLEANING A CHAMBER CONFIGURED FOR COPPER DEPOSITION | DING, PEIJUN |
| 09375167 | 6328871 | 150 | 08/16/1999 7X | BARRIER LAYER FOR ELECTROPLATING PROCESSES | DING, PEIJUN |
| 09378364 | Not Issued | 161 | 08/20/1999 | SEQUENTIAL SPUTTER AND REACTIVE PRECLEANS OF VIAS AND CONTACTS | DING, PEIJUN |
| 09386077 | 6399479 | 150 | 08/30/1999 7 | NEW PROCESSES TO IMPROVE ELECTROPLATING FILL | DING, PEIJUN |
| 09388989 | Not Issued | 135 | 09/02/1999 | SEQUENTIAL SPUTTER AND REACTIVE PRECLEANS OF VIAS AND CONTACTS | DING, PEIJUN |
| 09414614 | 6398929 | 150 | 10/08/1999 7X | PLASMA REACTOR AND SHIELDS GENERATING SELF-IONIZED PLASMA FOR SPUTTERING | DING, PEIJUN |
| 09423470 | 6488823 | 150 | 11/04/1999 7X | STRESS TUNABLE TANTALUM AND TANTALUM NITRIDE FILMS | DING, PEIJUN |
| 09425082 | 6207558 | 150 | 10/21/1999 | BARRIER APPLICATIONS FOR ALUMINUM PLANARIZATION | DING, PEIJUN |
| 09430998 | 6200433 | 150 | 11/01/1999 77 | IMP TECHNOLOGY WITH HEAVY GAS SPUTTERING | DING, PEIJUN |
| 09440679 | 6458251 | 150 | 11/16/1999 7 | PRESSURE MODULATION METHOD TO OBTAIN IMPROVED STEP COVERAGE OF SEED LAYER | DING, PEIJUN |
| 09441032 | Not Issued | 161 | 11/16/1999 | METHOD AND APPARATUS FOR PHYSICAL VAPOR DEPOSITION USING MODULATED POWER | DING, PEIJUN |
| 09449202 | 6350353 | 150 | 11/24/1999 7 | ALTERNATE STEPS OF IMP AND SPUTTERING PROCESS TO IMPROVE SIDEWALL COVERAGE | DING, PEIJUN |
| 09478721 | 6160315 | 150 | 01/06/2000 7X | COPPER ALLOY VIA STRUCTURE | DING, PEIJUN |

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|-----------------|------------|--------|------------|---|---------------|
| <u>09524239</u> | 6299689 | 150 | 03/13/2000 | Reflow chamber and process | DING, PEIJUN |
| <u>09538343</u> | 6607640 | 150 | 03/29/2000 | TEMPERATURE CONTROL OF A SUBSTRATE | DING, PEIJUN |
| <u>09561039</u> | Not Issued | 161 | 04/28/2000 | Method and apparatus for reducing overhang in ionized metal plasma systems | DING, PEIJUN |
| <u>09611624</u> | Not Issued | 161 | 07/07/2000 | Stress tunable tantalum and tantalum nitride films | DING, PEIJUN |
| <u>09618364</u> | Not Issued | 161 | 07/18/2000 | TEMPERATURE CONTROLLED SPUTTERING OF LOW COMPRESSIVE STRESS BARRIER LAYERS | DING, PEIJUN |
| <u>09626850</u> | Not Issued | 161 | 07/27/2000 | Tantalum-containing barrier layers for copper using high purity tantalum targets for sputtering | DING, PEIJUN |
| <u>09649507</u> | Not Issued | 161 | 08/28/2000 | METHOD AND APPARATUS FOR DEPOSITING A NITROGEN CONTAINING FILM FOR LOW-K APPLICATIONS | DING, PEIJUN |
| <u>09650108</u> | 6436267 | 150 | 08/29/2000 | METHOD FOR ACHIEVING COPPER FILL OF HIGH ASPECT RATIO INTERCONNECT FEATURES | DING, PEIJUN |
| <u>09685978</u> | 6582569 | 150 | 10/10/2000 | PROCESS FOR SPUTTERING COPPER IN A SELF IONIZED PLASMA | DING, PEIJUN |
| <u>09685988</u> | 6413383 | 150 | 10/10/2000 | METHOD FOR IGNITING A PLASMA IN A SPUTTER REACTOR | DING, PEIJUN |
| <u>09691687</u> | Not Issued | 161 | 10/18/2000 | PVD-IMP tungsten and tungsten nitride as a liner, barrier, and/or seed layer for tungsten, aluminum | DING, PEIJUN |

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|---------------------|----------------|-----|------------|---|--------------|
| | | | | and copper applications | |
| <u>09709991</u> | <u>6352926</u> | 150 | 11/10/2000 | Structure for improving low temperature copper reflow in semiconductor features | DING, PEIJUN |
| <u>09710383</u> | <u>6566259</u> | 150 | 11/09/2000 | INTEGRATED-DEPOSITION PROCESS FOR COPPER METALLIZATION | DING, PEIJUN |
| <u>09725595</u> | <u>6375743</u> | 150 | 11/29/2000 | METHOD FOR IMPROVED CHAMBER BAKE-OUT AND COOL-DOWN | DING, PEIJUN |
| <u>09770934</u> | <u>6458255</u> | 150 | 01/25/2001 | ULTRA-LOW RESISTIVITY TANTALUM FILMS AND METHODS FOR THEIR DEPOSITION | DING, PEIJUN |
| 09775356 | Not Issued | 161 | 01/31/2001 | Method of obtaining low temperature alpha-Ta thin films using wafer bias | DING, PEIJUN |
| <u>09784709</u> | <u>6368880</u> | 150 | 02/14/2001 | Barrier applications for aluminum planarization | DING, PEIJUN |
| 09805865 | Not Issued | 161 | 03/13/2001 | Integrated barrier layer structure for copper contact level metallization | DING, PEIJUN |
| 09829547 | Not Issued | 161 | 04/09/2001 | Burn-in process for high density plasma PVD chamber | DING, PEIJUN |
| <u>09886439</u> | <u>6758947</u> | 150 | 06/20/2001 | DAMAGE-FREE SCULPTURED COATING DEPOSITION | DING, PEIJUN |
| <u>09908829</u> | <u>6579730</u> | 150 | 07/18/2001 | MONITORING PROCESS FOR OXIDE REMOVAL | DING, PEIJUN |
| <u>09916412</u> | <u>6627050</u> | 150 | 07/26/2001 | METHOD AND APPARATUS FOR DEPOSITING A TANTALUM-CONTAINING LAYER ON A SUBSTRATE | DING, PEIJUN |
| <u>09993543</u> | <u>6610184</u> | 150 | 11/14/2001 | MAGNET ARRAY IN CONJUNCTION WITH ROTATING MAGNETRON FOR PLASMA SPUTTERING | DING, PEIJUN |
| <u>10016255</u> | <u>6790776</u> | 150 | 12/10/2001 | BARRIER LAYER FOR ELECTROPLATING PROCESSES | DING, PEIJUN |
| <u>10016350</u> | <u>6580057</u> | 150 | 12/10/2001 | ENHANCED COOLING IMP COIL SUPPORT | DING, PEIJUN |
| 10037172 | Not Issued | 161 | 11/07/2001 | Alternate steps of IMP and sputtering process to improve sidewall coverage | DING, PEIJUN |
| 10060827 | Not | 161 | 01/29/2002 | Stress tunable tantalum and | DING, PEIJUN |

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|---------------------|------------|-----|------------|---|--------------|
| | Issued | | | tantalum nitride films | |
| 10146416 | Not Issued | 161 | 05/14/2002 | METHODS OF PRODUCING ULTRA -LOW RESISTIVITY TANTALUM FILMS. | DING, PEIJUN |
| 10152494 | 6841050 | 150 | 05/21/2002 | SMALL PLANETARY MAGNETRON | DING, PEIJUN |
| 10180225 | Not Issued | 161 | 06/26/2002 | Method for achieving copper fill of high aspect ratio interconnect features | DING, PEIJUN |
| 10202778 | Not Issued | 161 | 07/25/2002 | Self-ionized and inductively-coupled plasma for sputtering and resputtering | DING, PEIJUN |
| 10246316 | 6911124 | 150 | 09/17/2002 | METHOD OF DEPOSITING A TAN SEED LAYER | DING, PEIJUN |
| 10262652 | Not Issued | 41 | 09/30/2002 | Pressure modulation method to obtain improved step coverage of seed layer | DING, PEIJUN |
| 10326496 | 6893541 | 150 | 12/20/2002 | MULTI-STEP PROCESS FOR DEPOSITING COPPER SEED LAYER IN A VIA | DING, PEIJUN |
| 10369856 | 6793779 | 150 | 02/20/2003 | SPUTTERING METHOD FOR FILLING HOLES WITH COPPER | DING, PEIJUN |
| 10418710 | 6852202 | 150 | 04/17/2003 | SMALL EPICYCLIC MAGNETRON WITH CONTROLLED RADIAL SPUTTERING PROFILE | DING, PEIJUN |
| 10421174 | 6881673 | 150 | 04/22/2003 | INTEGRATED DEPOSITION PROCESS FOR COPPER METALLIZATION | DING, PEIJUN |
| 10439021 | Not Issued | 161 | 05/14/2003 | Method and apparatus for sputter deposition | DING, PEIJUN |
| 10495506 | Not Issued | 30 | 05/12/2004 | Self-ionized and inductively-coupled plasma for sputtering and resputtering | DING, PEIJUN |
| 10608306 | Not Issued | 61 | 06/26/2003 | Sidewall magnet improving uniformity of inductively coupled plasma and shields used therewith | DING, PEIJUN |
| 10643281 | Not Issued | 41 | 08/18/2003 | One or more shields for use in a sputter reactor | DING, PEIJUN |
| 10646014 | 6875321 | 150 | 08/22/2003 | AUXILIARY MAGNET ARRAY IN CONJUNCTION WITH MAGNETRON SPUTTERING | DING, PEIJUN |
| 10755644 | Not Issued | 92 | 01/12/2004 | ROTATIONAL AND RECIPROCAL RADIAL | DING, PEIJUN |

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|-----------------|----------------|-----|-----------------|---|--------------|
| | | | | MOVEMENT OF A SPUTTERING MAGNETRON | |
| <u>10796602</u> | <u>6919275</u> | 150 | 03/08/2004 7 | METHOD OF PREVENTING DIFFUSION OF COPPER THROUGH A TANTALUM- COMPRISING BARRIER LAYER | DING, PEIJUN |
| <u>10862257</u> | Not Issued | 61 | 06/07/2004 X | Magnetron executing planetary motion adjacent a sputtering target | DING, PEIJUN |
| <u>10915139</u> | Not Issued | 30 | 08/09/2004 ? | Sputter deposition and etching of metallization seed layer for overhang and sidewall improvement | DING, PEIJUN |
| <u>10922052</u> | Not Issued | 30 | 08/18/2004 ? | Method of depositing a diffusion barrier layer and a metal conductive layer | DING, PEIJUN |
| <u>10931865</u> | Not Issued | 41 | 09/01/2004 ? | Barrier layer for electroplating processes | DING, PEIJUN |
| <u>10940518</u> | Not Issued | 41 | 09/14/2004 ? | TWO STEP METHOD FOR FILLING HOLES WITH COPPER | DING, PEIJUN |
| <u>10942273</u> | Not Issued | 30 | 09/16/2004 X | Mechanism for varying the spacing between sputter magnetron and target | DING, PEIJUN |

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|-----------------|----------------|--------|------------|---|---------------|
| <u>10942358</u> | Not Issued | 30 | 09/16/2004 | Compensation of spacing between magnetron and sputter target | DING, PEIJUN |
| <u>10981319</u> | Not Issued | 30 | 11/03/2004 | Method of depositing a metal seed layer on semiconductor substrates | DING, PEIJUN |
| <u>11069348</u> | Not Issued | 30 | 02/28/2005 | Method of depositing a tantalum nitride / tantalum diffusion barrier layer system | DING, PEIJUN |
| <u>11124524</u> | Not Issued | 30 | 05/05/2005 | Shields usable with an inductively coupled plasma reactor. | DING, PEIJUN |
| <u>11184404</u> | Not Issued | 20 | 07/18/2005 | Method of depositing low resistivity barrier layers for copper interconnects | DING, PEIJUN |
| <u>11184615</u> | Not Issued | 30 | 07/19/2005 | Self-ionized and inductively-coupled plasma for sputtering and resputtering | DING, PEIJUN |
| <u>29090631</u> | <u>D440582</u> | 150 | 07/13/1998 | SPUTTERING CHAMBER COIL | DING, PEIJUN |
| <u>60067108</u> | Not Issued | 159 | 12/02/1997 | INTEGRATED DEPOSITION PROCESS FOR COPPER METALLIZATION | DING, PEIJUN |
| <u>60159986</u> | Not Issued | 159 | 10/18/1999 | PVD-IMP TUNGSTEN AND TUNGSTEN NITRIDE AS A LINER, BARRIER, AND/OR SEED LAYER FOR TUNGSTEN, ALUMINUM AND COPPER APPLICATIONS | DING, PEIJUN |
| <u>60221597</u> | Not Issued | 159 | 07/28/2000 | SIP TA/TAN barrier layer for copper metallization | DING, PEIJUN |
| <u>60284496</u> | Not Issued | 159 | 04/18/2001 | Process for depositing metal seed layer on a substrate | DING, PEIJUN |
| <u>60306698</u> | Not Issued | 159 | 07/20/2001 | Low resistivity tantalum nitride/tantalum bilayer stack | DING, PEIJUN |
| <u>60316137</u> | Not | 159 | 08/30/2001 | Self-ionized and inductively- | DING, PEIJUN |

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|--------------------------|------------|-----|------------|--|--------------|
| | Issued | | | coupled plasma for sputtering | |
| 60342608 | Not Issued | 159 | 12/21/2001 | Self-ionized and inductively-coupled plasma for sputtering and resputtering | DING, PEIJUN |
| 60380385 | Not Issued | 159 | 05/14/2002 | Method and apparatus for sputter deposition | DING, PEIJUN |
| 60441866 | Not Issued | 159 | 01/22/2003 | Small epicyclic magnetron with controlled radial sputtering profile | DING, PEIJUN |
| 60465556 | Not Issued | 159 | 04/25/2003 | Diode laser systems with multiple wavelengths for skin rejuvenation and other dermatological applications | DING, PEIJUN |
| 60465557 | Not Issued | 159 | 04/25/2003 | Diode laser systems with multiple wavelengths for hair removal, pigmented lesion and vascular lesion treatment | DING, PEIJUN |
| 60529209 | Not Issued | 159 | 12/12/2003 | Compensation of spacing between magnetron and sputter target | DING, PEIJUN |

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